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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/747,848	12/21/2000	Vladislav Vashchenko	NSC1-H2000 (P04846)	4415

27271 7590 01/16/2002

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EXAMINER

NADAV, ORI

ART UNIT	PAPER NUMBER
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2811

DATE MAILED: 01/16/2002

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Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/747,848

Applicant(s)

VASHCHENKO ET AL.

Examiner

ori nadav

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 15 August 2001.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-11 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-11 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on _____ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____
- 4) ☐ Interview Summary (PTO-413) Paper No(s). _____
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: _____

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

2. Claims 1-3, 5-6 and 10-11 are rejected under 35 U.S.C. 102(a) as being anticipated by Admitted Prior Art (APA).

APA teaches in figure 1 and related text an ESD protection structure for use with RF frequency integrated circuits comprising: a P- epitaxial silicon semiconductor substrate 12; an N- well region 14 disposed in the semiconductor substrate; a P+ first region 16 disposed in the N-well region on the P- epitaxial silicon semiconductor substrate; an N+ second region 18 disposed in and on the P- epitaxial silicon semiconductor substrate and spaced apart from the P+ first region; and a shallow trench isolation region 20 disposed in the P- epitaxial silicon semiconductor substrate between the P+ first region and the N+ second region, wherein the maximum dopant concentration of the semiconductor substrate is less than the maximum dopant concentration of the first region and the maximum dopant concentration of the well region is less than the

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maximum dopant concentration of the second region, and having a bottom contact to the semiconductor substrate (not shown).

Note that since N- well region 14 is disposed in the semiconductor substrate and N+ second region 18 is disposed in N- well region 14, then N+ second region 18 is disposed in and on the P- epitaxial silicon semiconductor substrate.

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

4. Claims 4 and 7-9 are rejected under 35 U.S.C. 103(a) as being unpatentable over APA.

APA teaches substantially the entire claimed structure, as applied to claims 1-3 above, except dopant concentration of the semiconductor substrate is 5×10^{15} atoms/cm³, the maximum dopant concentration of the well region is 2×10^{17} atoms/cm³, the maximum dopant concentration of the first region is 5×10^{20} atoms/cm³, the maximum dopant concentration of the second region is 5×10^{20} atoms/cm³, and the P- epitaxial silicon layer has a dopant concentration no greater than 5×10^{15} atoms/cm³.

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It would have been obvious to a person of ordinary skill in the art at the time the invention was made to use dopant concentration of the semiconductor substrate is 5×10^{15} atoms/cm³, the maximum dopant concentration of the well region is 2×10^{17} atoms/cm³, the maximum dopant concentration of the first region is 5×10^{20} atoms/cm³, the maximum dopant concentration of the second region is 5×10^{20} atoms/cm³, and the P- epitaxial silicon layer has a dopant concentration no greater than 5×10^{15} atoms/cm³. in APA's device, since it is a matter of design choice within the skills of an artisan, subject to routine experimentation and optimization.

Regarding claim 8, APA teaches configuring the ESD device between an input/output line of an integrated circuit and GND.

Regarding claim 9, it would have been obvious to a person of ordinary skill in the art at the time the invention was made to configure APA's device between a VDD line of the integrated circuit and a differential amplifier of the integrated circuit in order to use the device in a specific application.

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. References A-C and N are cited as being related to ESD devices.

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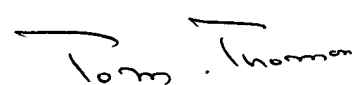
Papers related to this application may be submitted to Technology center (TC) 2800 by facsimile transmission. Papers should be faxed to TC 2800 via the TC 2800 Fax center located in Crystal Plaza 4, room 4-C23. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Group 2811 Fax Center number is (703) 308-7722 and 308-7724. The Group 2811 Fax Center is to be used only for papers related to Group 2811 applications.

Any inquiry concerning this communication or any earlier communication from the Examiner should be directed to *Examiner Nadav* whose telephone number is **(703) 308-8138**. The Examiner is in the Office generally between the hours of 7 AM to 3 PM (Eastern Standard Time) Monday through Friday. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Tom Thomas, can be reached at **(703) 308-2772**.

Any inquiry of a general nature or relating to the status of this application should be directed to the **Technology Center Receptionists** whose telephone number is **308-0956**

Ori Nadav

January 10, 2002


**TOM THOMAS
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800**